SIlicon Power

Industrial 3D TLC NAND M.2 2280 NVMe SSD

MEC3H0S SERIES

PCIe Gen4x4	TCG Opal 2.0
3K PE Cycles	R/W: 7,200 / 6,500 MB/s



PRODUCT FEATURES

- High-Quality 112-layer 3D TLC NAND Flash Technology.
- Industrial Standard PCIe Gen4x4 with NVMe 1.4 Compliant.
- Support TRIM command to remove data not in use to keep optimized performance.
- Dynamic SLC caching algorithm to deliver the better sustained performance.
- "Predict & Fetch" mechanism to improve read performance.
- When SSD is going to worn-out to activate Read Only Mode to prevent further data corruption.
- Lifetime Enhancements

Support Both Dynamic wear leveling and Static wear leveling. Early bad block detect and Later bad block management. Over-provisioning to reserve extra space to enhance reliability and endurance.. Block/Page RAID function to ensure data recovery.

- Reliable Industrial grade integrated Active PMU and complete protection design with OVP, OCP, surge rejection and Short protection.
- External DRAM to achieve the optimal sustained read/write performance.
- Power shielding firmware architecture to ensure power failure resilience.
- AES256 Encryption and TCG Opal 2.0 compliant.
- SP SMART Toolbox.
- SP SMART Embedded and SMART IoT service. (by request)
- Driven by a growing number of IOPS in heavy data applications, the biggest benefit of PCIe-based SSD is increased performance.
 Reach up to R:7200 MB/s and W:6500 MB/s based on 32CE NAND flash.

PRODUCT SUMMARY

- Capacities : 480GB, 960GB, 1920GB, 3840GB
- Form Factor : M.2 2280 PCIe Solid State Drive (80 mm x 22 mm x 3.5 mm)
- Compliance : PCIe Gen 4x4 compliant with Gen1,2,3.
- Command Sets :NVMe1.4 standard command protocol.
- Performance :

	480GB	960GB	1920GB	3840GB	
Sequential Read (MB/s Max.)	6,500	7,200	7,200	7,200	
Sequential Write (MB/s Max.)	3,000	6,000	6,500	6,500	
Random 4K Read (IOPS Max.)	450,000	750,000	750,000	750,000	
Random 4K Write (IOPS Max.)	700,000	1,000,000	1,000,000	1,000,000	

* Actual performance may vary based on the specific model and capacity

Operating Temperature Range :

Normal : 0°C to 70°C

Wide : -40°C to 85°C (by request)

- Storage Temperature Range : -55°C to 95°C
- Operating Voltage : 3.3 V ± 10%
- Power Consumption :

(Unit: W)	480GB	960GB	1920GB	3840GB	
Read (Max.)	8.8	10.1	10.6	10.9	
Write (Max.)	7.5	9.4	10.5	11.0	
Stand-by (Avg.)	<3.4	<3.4	<3.6	<3.6	

* Actual value may vary based on the specific model and capacity

Data Retention @40 °C : 10 Years @ Life Begin; 1 Year @ Life End

• Endurance in Tera Bytes Written (TBW) : (Unit: TB)

Workload	480GB	960GB	1920GB	3840GB
Sequential	350	750	1400	3000
Enterprise	TBD	TBD	TBD	TBD

TBW is estimated by formula TBW = (Capacity x PE Cycles) x (1+OP) x (WLE) / (WAF)

OP (Over Provision) = (Physical Capacity / Logical Capacity)-1

WAF = Write Amplification Factor

WLE = Wear Leveling Efficiency could be different depended on the workload or usage containing data size and access rate.
 Sequential workload: Sequential write workload which is generated by VDBENCH script and tested by VDBENCH
 Enterprise workload: Follow JESD219A enterprise workload which is generated by VDBENCH script and tested by VDBENCH.

Mechanical (IEC-60068):

Vibration : 15G, 10 ~ 2001Hz Drop : 76cm Shock : 1,500G@0.6ms

- LDPC ECC engine and Block/Page RAID to ensure reliable 3K PE cycles
- Mean Time Between Failure : > 2,000,000 hours
- Data Reliability: Non-recover Read (UBER) ≤10⁻¹⁶
- · Serious quality control and assurance

100% NAND Flash screening

High endurance product design with 3D NAND product offerings

Implement high/low temperature dynamic burn-in in each lot production to monitor production quality to meet design specification Reliability criteria compliant with international standards IEC-60068/61000

